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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yi-Fan Chen, Chi-King Pu, Shou-Kong Fan
Examiner: Huynh, Andy
Filing Date: 04/18/01
Art Unit: 2818
Serial No.: 09/836,258
Docket No.: NAUP0280USA

Title: BYPASS CIRCUITS FOR REDUCING PLASMA DAMAGE

To: The Commissioner of Patents and Trademarks
Washington, D.C. 20231

Subject: Response to the Office Action dated 05/03/2002

Dear Sir:

AMENDMENT

In response to the Office Action identified above, please amend the above-identified application as follows:

In the claims:

1. (Once amended) A bypass circuit for reducing plasma damage to a gate oxide of a metal-oxide semiconductor (MOS) wafer, the bypass circuit positioned on a semiconductor wafer, the semiconductor wafer comprising a substrate, the MOS transistor, a dielectric layer, and the bypass circuit, respectively, with the bypass circuit comprising: